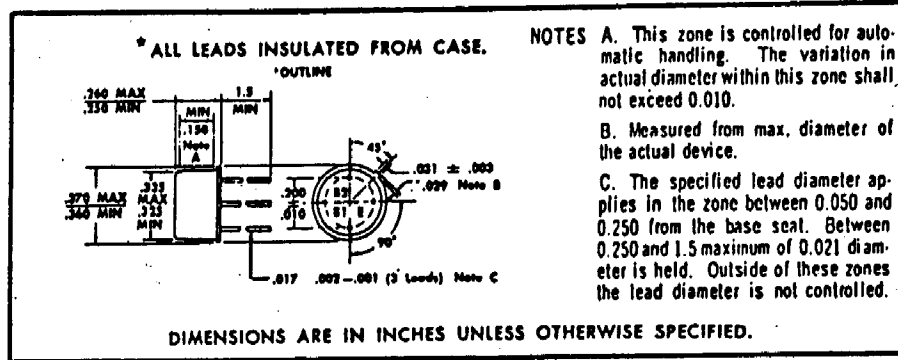


## 2N1671B Silicon Unijunction Transistors



### absolute maximum ratings (25°C)

RMS Power Dissipation	450 mw
RMS Emitter Current	50 ma
Peak Emitter Current	2 amperes
Emitter Reverse Voltage	30 volts
Interbase Voltage	35 volts
Operating Temperature Range	-65°C to +140°C
Storage Temperature Range	-65°C to +150°C

### electrical characteristics (25°C)

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
Intrinsic Standoff Ratio ( $V_{BB} = 10V$ )	$\eta$	0.47	0.62	
Interbase Resistance ( $V_{BB} = 3V, I_E = 0$ )	$R_{BB}$	4.7	0.1	K $\Omega$
Emitter Saturation Voltage ( $V_{BB} = 10V, I_E = 50$ ma)	$V_E(SAT)$		5	volts
Modulated Interbase Current ( $V_{BB} = 10V, I_E = 50$ ma)	$I_{BB}(MOD)$	6.8	22	ma
Emitter Reverse Current ( $V_{BB} = 30V, I_{B1} = 0$ )	$I_{E0}$		0.2	$\mu A$
Peak Point Emitter Current ( $V_{BB} = 25V$ )	$I_P$		6	$\mu A$
Valley Point Current ( $V_{BB} = 20V, R_{BB} = 100\Omega$ )	$I_V$	8		ma
Base-One Peak Pulse Voltage	$V_{OB1}$	3.0		volts

